

BLF888D; BLF888DS

UHF power LDMOS transistor

Rev. 1 — 5 March 2014

Objective data sheet

1. Product profile

1.1 General description

A 600 W LDMOS RF power transistor for broadcast Doherty transmitter applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Table 1. Application information

RF performance at $V_{DS} = 50$ V in an ultra wide Doherty application.

Test signal	f (MHz)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	IMD_{shldr} (dBc)	PAR (dB)
DVB-T (8k OFDM)	470 to 806	115 to 134 [2]	17	40 to 48 [2]	-38 to -44 [3]	8 [1]

[1] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

[2] Depending on selected channel.

[3] Depending on exciter used.

1.2 Features and benefits

- High efficiency
- High power gain
- Excellent ruggedness (VSWR \geq 40 : 1 through all phases)
- Excellent thermal stability
- Integrated ESD protection
- One Doherty design covers the full bandwidth from 470 MHz to 806 MHz
- Internal input matching for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

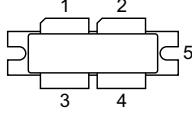
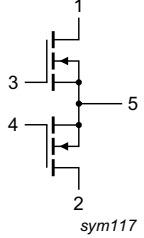
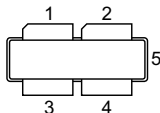
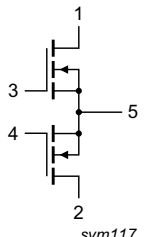
1.3 Applications

- Broadcast transmitter applications in the UHF band
- Digital broadcasting



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF888D (SOT539A)			
1	drain1 (peak)		 sym117
2	drain2 (main)		
3	gate1 (peak)		
4	gate2 (main)		
5	source [1]		
BLF888DS (SOT539B)			
1	drain1 (peak)		 sym117
2	drain2 (main)		
3	gate1 (peak)		
4	gate2 (main)		
5	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF888D	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A
BLF888DS	-	earless flanged balanced ceramic package; 4 leads	SOT539B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+11	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 75\text{ °C}; V_{DS} = 50\text{ V};$ [1] $I_{DS} = 2.7\text{ A (main)}; I_{DS} = 0\text{ A (peak)}$	0.27	K/W
		$T_{case} = 90\text{ °C}; V_{DS} = 50\text{ V};$ [2] $P_L = 115\text{ W}; PAR = 8\text{ dB}$	0.16	K/W

[1] Measured under DC test conditions, with peak section off.

[2] Measured in an ultra wide Doherty application, using a DVB-T (8k OFDM) signal, PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ °C};$ per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 2.4\text{ mA}$	104	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 240\text{ mA}$	1.4	1.9	2.4	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}$	-	0.061	2.8	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	-	37	-	A
I_{GSS}	gate leakage current	$V_{GS} = 10\text{ V}; V_{DS} = 0\text{ V}$	-	-	280	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 8.5\text{ A}$	-	120	-	$\text{m}\Omega$

Table 7. AC characteristics

$T_j = 25\text{ °C};$ per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	210	-	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	70	-	pF
C_{rss}	reverse transfer capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}; f = 1\text{ MHz}$	-	1.3	-	pF

Table 8. RF characteristics

$V_{DS} = 50\text{ V}; I_{Dq} = 1.3\text{ A}; T_{case} = 25\text{ °C}$ unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Test signal: 2-tone CW						
$P_{L(AV)}$	average output power	$f_1 = 860\text{ MHz}; f_2 = 860.1\text{ MHz}$	-	250	-	W
G_p	power gain	$f_1 = 860\text{ MHz}; f_2 = 860.1\text{ MHz}$	19	21	-	dB
η_D	drain efficiency	$f_1 = 860\text{ MHz}; f_2 = 860.1\text{ MHz}$	43	45	-	%
IMD3	third-order intermodulation distortion	$f_1 = 860\text{ MHz}; f_2 = 860.1\text{ MHz}$	-	-32	-29	dBc
Test signal: pulsed CW						
$P_{L(3dB)}$	output power at 3 dB gain compression	$f = 860\text{ MHz}; t_p = 100\text{ }\mu\text{s};$ $\delta = 10\%$	540	580	-	dB

7. Test information

7.1 Ruggedness in Doherty operation

The BLF888D and BLF888DS are capable of withstanding a load mismatch corresponding to $V_{SWR} \geq 40 : 1$ through all phases under the following conditions:
 $V_{DS} = 50 \text{ V}$; $f = 810 \text{ MHz}$ at rated load power.

8. Package outline

Flanged balanced ceramic package; 2 mounting holes; 4 leads

SOT539A

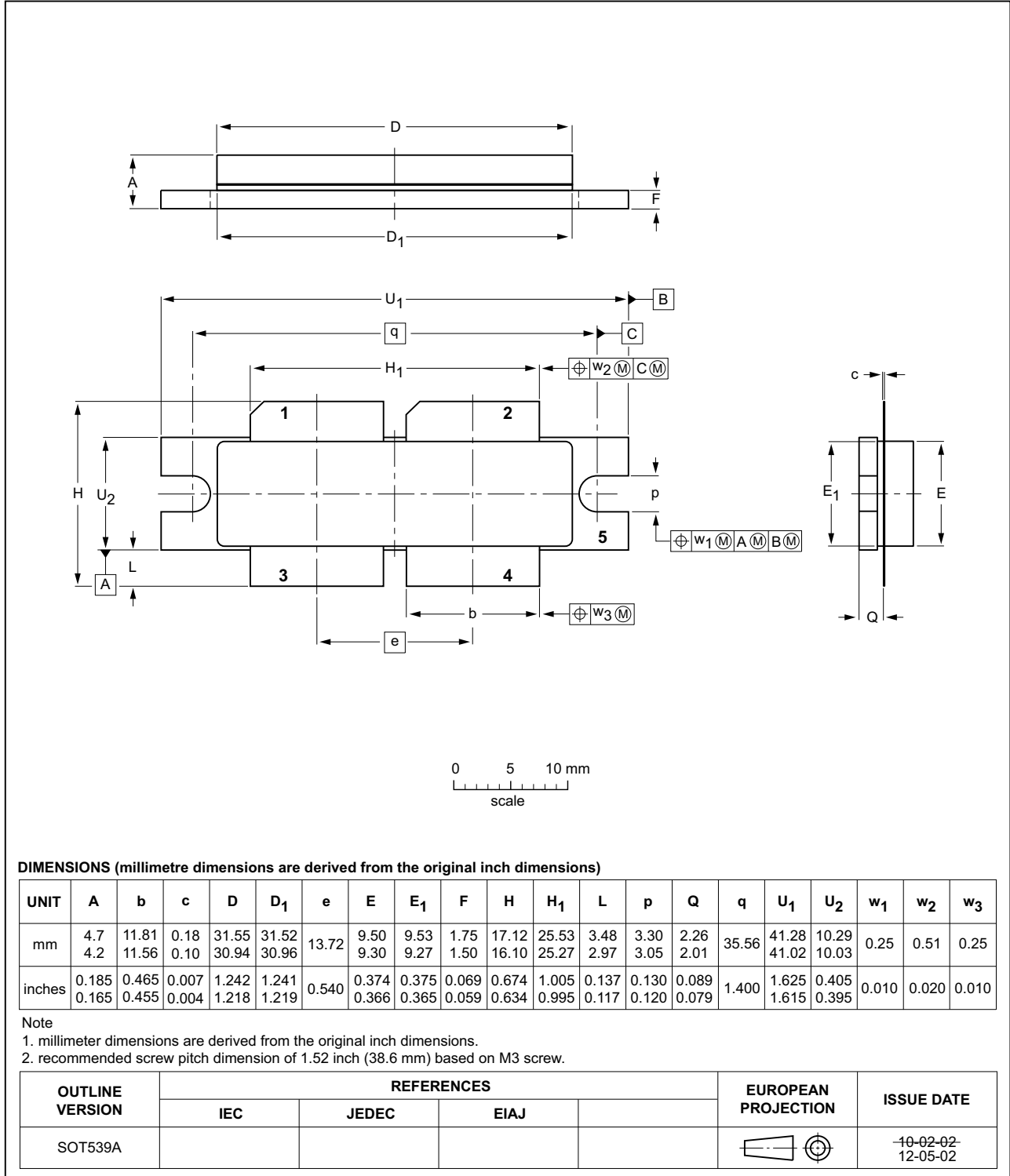


Fig 1. Package outline SOT539A

Earless flanged balanced ceramic package; 4 leads

SOT539B

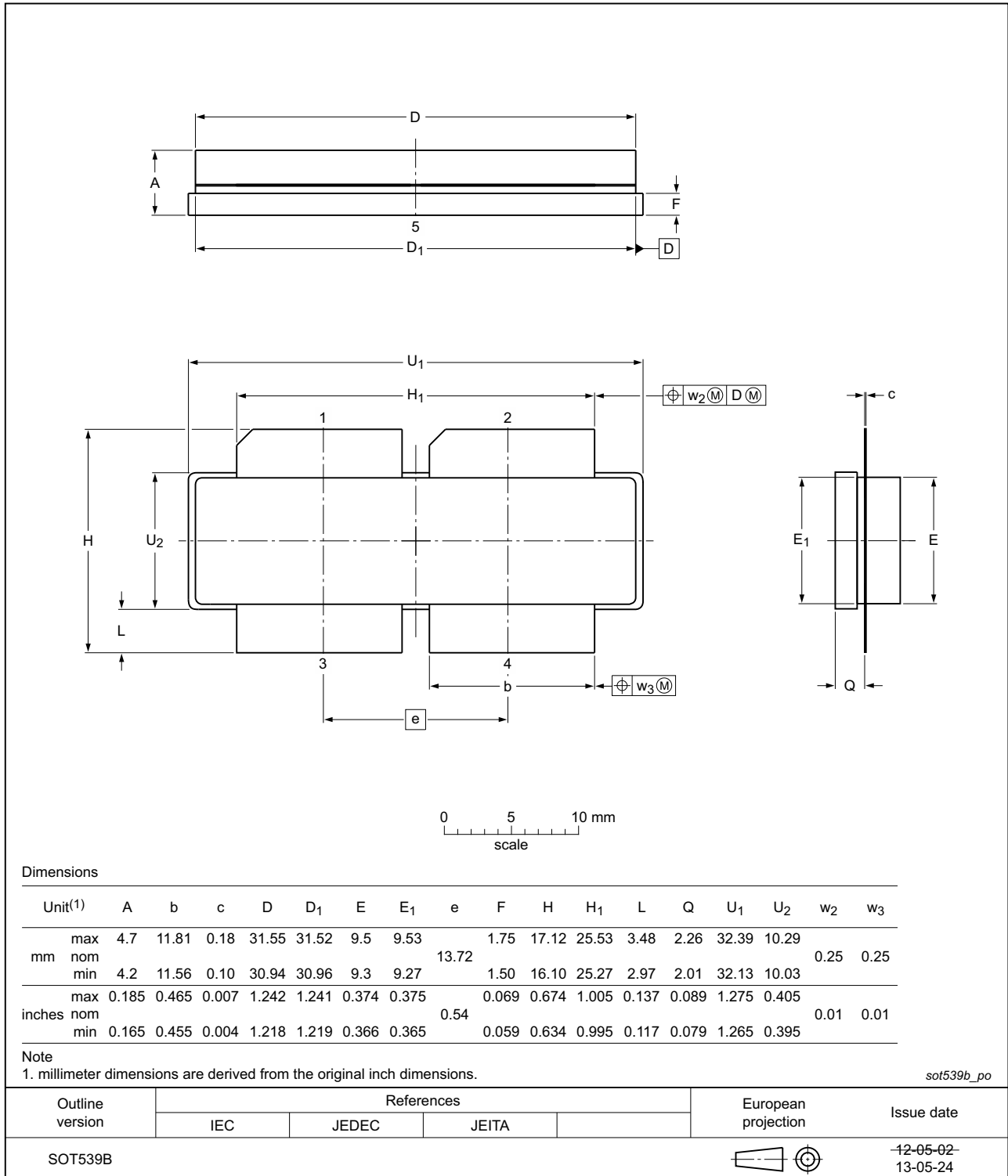


Fig 2. Package outline SOT539B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average Ratio
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF888D_BLF888DS v.1	20140305	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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